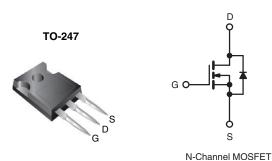


Vishay Siliconix

Power MOSFET



PRODUCT SUMMARY			
V _{DS} (V) at T _J max.	560		
$R_{DS(on)}(\Omega)$	$V_{GS} = 10 \text{ V}$	0.270	
Q _g max. (nC)	76		
Q _{gs} (nC)	21		
Q _{gd} (nC)	34		
Configuration	Single		

FEATURES

- Low figure-of-merit Ron x Qa
- 100 % avalanche tested
- · High peak current capability
- dv/dt ruggedness
- Improved T_{rr}/Q_{rr}
- Improved gate charge
- · High power dissipations capability
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION		
Package	TO-247AC	
Lead (Pb)-free	SiHG20N50C-E3	

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	500	V
Gate-source voltage			V_{GS}	± 30]
Continuous drain surrent (T = 150 °C) 8	V at 10 V	T _C = 25 °C		20	
Continuous drain current ($T_J = 150 ^{\circ}\text{C}$) a V_{GS} at 10 V $T_{C} = 100 ^{\circ}$		T _C = 100 °C	I _D	11	Α
Pulsed drain current ^b			I _{DM}	80	
Linear derating factor				1.8	W/°C
Single pulse avalanche energy c			E _{AS}	361	mJ
Maximum power dissipation			P_{D}	250	W
Reverse diode dV/dt ^d			dV/dt	5	V/ns
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) d For 10 s				300	1

- a. Limited by maximum junction temperature
- b. Repetitive rating; pulse width limited by maximum junction temperature
- c. V_{DD} = 50 V, starting T_J = 25 °C, L = 2.5 mH, R_g = 25 Ω , I_{AS} = 17 A
- d. $I_{SD} \le 18 \text{ A}$, di/dt $\le 380 \text{ A/µs}$, $V_{DD} \le V_{DS}$, $T_J \le 150 \text{ °C}$
- e. 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	0.5	C/VV



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_{D}$	= 250 µA	500	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to	25 °C, I _D = 1 mA	-	0.7	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D}$	₀ = 250 μA	3.0	-	5.0	V
Gate-source leakage	I _{GSS}	$V_{GS} = \pm 30 \text{ V}$		-	-	± 100	nA
Zava cata valtaca drain augrent	1	$V_{DS} = 500 \text{ V},$	V _{GS} = 0 V	-	-	25	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 400 \text{ V},$	V _{GS} = 0 V, T _J = 125 °C	-	-	250	μΑ
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.225	0.270	Ω
Forward transconductance	9 _{fs}	V _{DS} = 50 V, I	_D = 10 A	-	6.4	-	S
Dynamic							
Input capacitance	C _{iss}	$V_{GS} = 0 V$		-	2451	2942	
Output capacitance	C _{oss}	$V_{DS} = 25 \text{ V},$	$V_{DS} = 25 \text{ V},$		300	360	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz		-	26	32	
Total gate charge	Q_g			-	65	76	
Gate-source charge	Q_{gs}	V _{GS} = 10 V	V _{GS} = 10 V I _D = 18 A, V _{DS} = 400 V		21	-	nC
Gate-drain charge	Q _{gd}	1			29	-	
Turn-on delay time	t _{d(on)}			-	80	-	
Rise time	t _r	1, 250, 10, 10, 10, 10, 10, 10, 10, 10, 10, 1		-	27	-	
Turn-off delay time	t _{d(off)}	$V_{DD} = 250 \text{ V},$	$I_D = 18 \text{ A}, R_g = 9.1 \Omega$	-	32	-	ns
Fall time	t _f	1		-	44	-	
Gate input resistance	R_{g}	f = 1 MHz, o	pen drain	-	1.1	-	Ω
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	20	
Pulsed diode forward current	I _{SM}			-	-	80	Α
Diode forward voltage	V _{SD}	T _J = 25 °C, I _S	_S = 18 A, V _{GS} = 0 V	-	-	1.5	V
Reverse recovery time	t _{rr}			-	503	-	ns
Reverse recovery charge	Q _{rr}	T _J = 25 °C, I _I	= s,	_	6.7	-	μC
Reverse recovery current	I _{RRM}	$T_J = 25 ^{\circ}\text{C}, I_F = I_S,$ $di/dt = 100 \text{A/}\mu\text{s}^{, \text{V}}_R = 35 \text{V}$		-	30	-	A



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

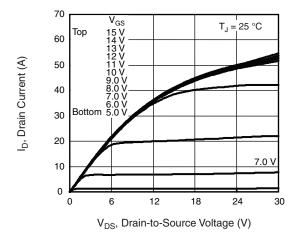


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

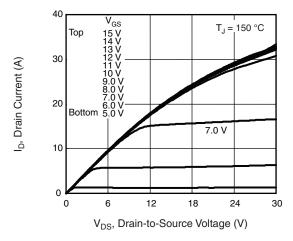


Fig. 2 - Typical Output Characteristics, $T_C = 150$ °C

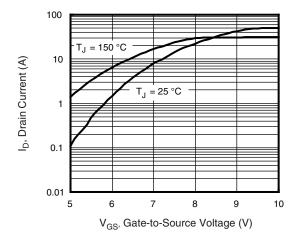


Fig. 3 - Typical Transfer Characteristics

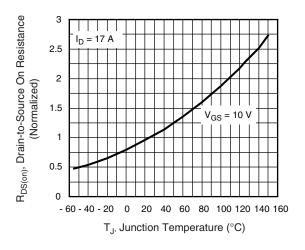


Fig. 4 - Normalized On-Resistance vs. Temperature

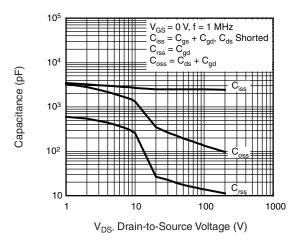


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

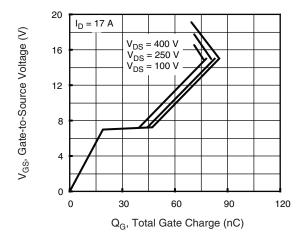
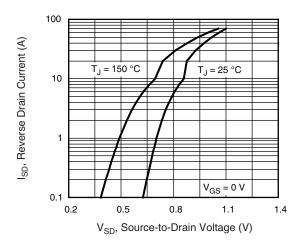


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage







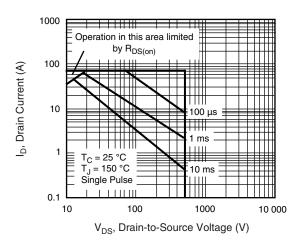


Fig. 8 - Maximum Safe Operating Area

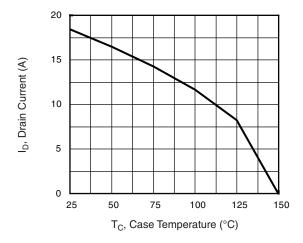


Fig. 9 - Maximum Drain Current vs. Case Temperature

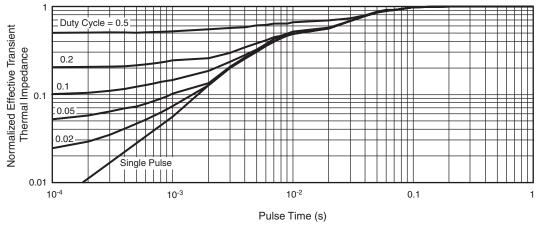


Fig. 10 - Normalized Thermal Transient Impedance, Junction-to-Case (TO-247)



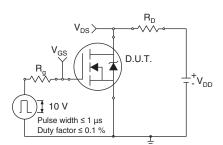


Fig. 11 - Switching Time Test Circuit

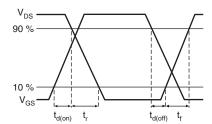


Fig. 12 - Switching Time Waveforms

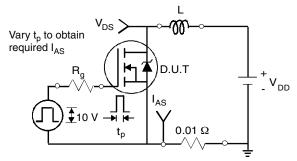


Fig. 13 - Unclamped Inductive Test Circuit

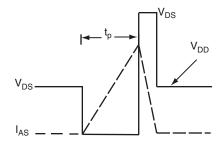


Fig. 14 - Unclamped Inductive Waveforms

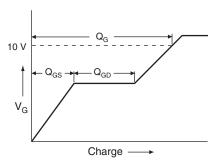


Fig. 15 - Basic Gate Charge Waveform

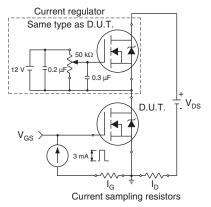
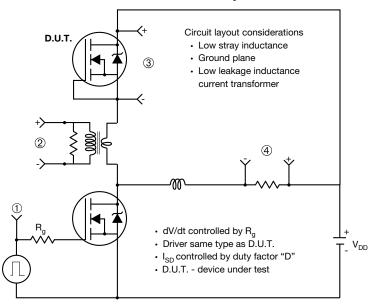


Fig. 16 - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



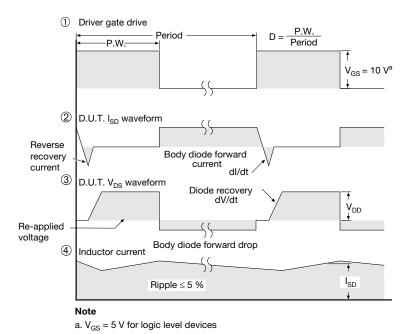


Fig. 17 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91382.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D-D,E-E

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES	
Α	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.17	1.27	1.37		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39	6	
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22	6, 8	
b5	2.87	3.00	3.18		
С	0.40	0.50	0.60	6	
c1	0.40	0.50	0.56		
D	20.40	20.55	20.70	4	

		MILLIMETERS	S	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
Е	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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VERSION 2: FACILITY CODE = Y



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIM	IETERS	
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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